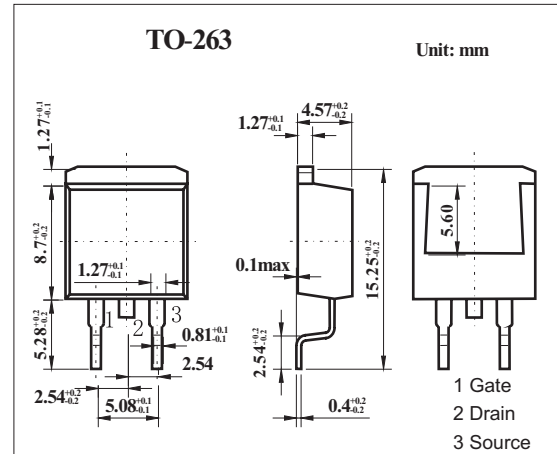
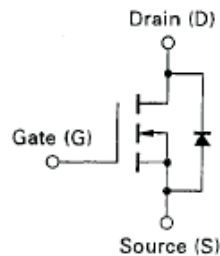


## MOS Field Effect Power Transistor 2SK2133

### ■ Features

- Low on-resistance  
 $R_{DS(on)}=0.21\ \Omega\ \text{MAX.}@V_{GS}=10V, I_D=8.0A$
- Low Ciss Ciss=1090 pF TYP.
- High avalanche capabil



### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	$V_{DS}$	250	V
Gate to source voltage	$V_{GS}$	$\pm 30$	V
Drain current	$I_D$	$\pm 16$	A
	$I_{dp}^*$	$\pm 64$	A
Power dissipation $T_A=25^\circ\text{C}$ $T_C=25^\circ\text{C}$	$P_D$	1.5	W
		75	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

\*  $PW \leq 10\ \mu\text{s}$ , Duty Cycle  $\leq 1\%$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit	
Drain cut-off current	$I_{DSS}$	$V_{DS}=250V, V_{GS}=0$			100	$\mu\text{A}$	
Gate leakage current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0$			$\pm 10$	$\mu\text{A}$	
Gate to source cutoff voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1\text{mA}$	2.0		4.0	V	
Forward transfer admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=8.0A$	4.0			S	
Drain to source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=8.0A$		0.2	0.26	$\Omega$	
Input capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0, f=1\text{MHZ}$		1090		pF	
Output capacitance	$C_{oss}$				420		pF
Reverse transfer capacitance	$C_{rss}$				80		pF
Turn-on delay time	$t_{d(on)}$	$I_D=8.0A, V_{GS(on)}=10V, R_L=18.75\ \Omega, R_G=10\ \Omega, V_{DD}=150V$		20		ns	
Rise time	$t_r$				40		ns
Turn-off delay time	$t_{d(off)}$				60		ns
Fall time	$t_f$				20		ns